

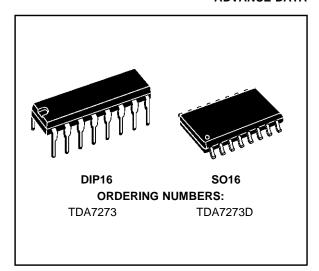
SINGLE CHIP STEREO CASSETTE PLAYBACK SYSTEM

ADVANCE DATA

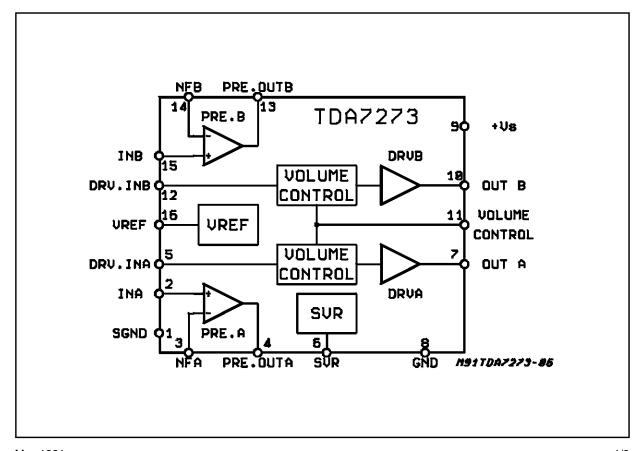
- WIDE OPERATING SUPPLY VOLTAGE (1.8V to 7V)
- INPUT COUPLING WITHOUT CAPACITORS
- BUILT-IN DC STEREO VOLUME CONTROL
- BUILT-IN RIPPLE FILTERS
- LOW QUIESCENT CURRENT
- NO EXTERNAL BOUCHEROT CELL
- MAX OUTPUT CURRENT 70mA PEAK

DESCRIPTION

The TDA7273 is a monolithic integrated circuit designed for portable cassette players market. It comprises preamplifiers, DC volume control, and headphone drivers.



BLOCK DIAGRAM



May 1991 1/9

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Test Conditions	Unit
Vs	Supply Voltage	9	V
Ιο	Output Current (max)	70	mA
T _{op}	Operating Temperature Range	-20 to 70	°C
T _{stg,} T _j	Storage & Junction Temperature Range	-40 to +150	°C

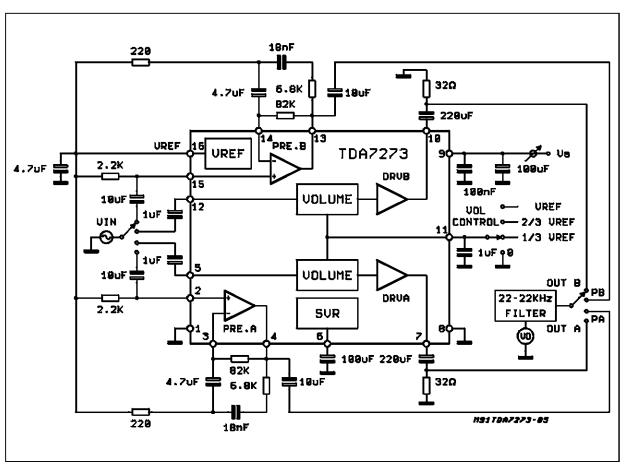
THERMAL DATA

Symbol	Description	DIP-16	SO-16	Unit
R _{thj-amb}	Thermal Resistance Junction-ambient Max	100	200	°C/W

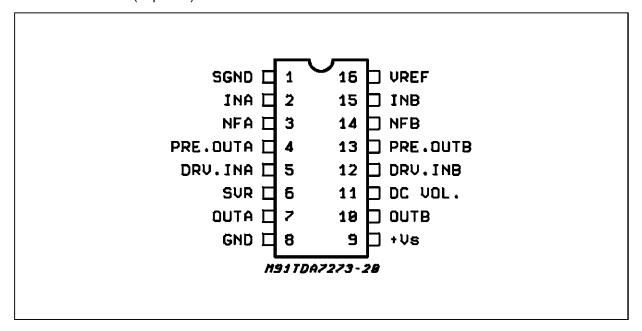
DC CHARACTERISTICS: $T_{amb} = 25^{\circ}C$; $V_S = 3V$; $R_L = 10K\Omega$ (Preamplifier), $R_L = 32\Omega$ (Headphone); $V_{IN} = 0$; V_{OL} control = V_{ref}

Terminal No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
Terminal Voltage (V)	0	1.5	1.5	1.5	1.5	2.7	1.5	0	3	1.5	1.5	1.5	1.5	1.5	1.5	1.5

TEST CIRCUIT



PIN CONNECTION (Top view)



ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $V_{S} = 3V$, f = 1 KHz, $R_{L} = 32 \Omega$ Vol. control = $2/3 V_{ref}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Vs	Supply Voltage		1.8		7	V
I _d	Quiescent Current			14	20	mA
Vref	Reference Voltage		1.3	1.49	1.7	V

PREAMPLIFIER SECTION

G _{VO}	Open Loop Gain			70		dB
G∨	Close Loop Gain		30	33	35	dB
Vo	Output Voltage	THD = 1%	600	850		mV
I _b	Bias Current			3		μΑ
THD	Total Harmonic Distortion	$V_0 = 330 \text{mVrms}$		0.05	0.25	%
Ct	Cross Talk	Rg = $2.2K\Omega$; V _o = 330 mVrms		74		dB
E _N	Output Noise	$Rg = 2.2K\Omega$; $BW = 22Hz$ to $22KHz$		100		μV
SVR	Ripple Rejection	$R_g = 2.2 \text{K}\Omega V_R = 100 \text{mVrms}$ $f = 100 \text{Hz}; C_{\text{SVR}} = 100 \mu \text{F}$	40	50		dB

HEADPHONE DRIVER

V _{o(DC)}	DC Output Voltage			1.50		V
Po	Output Power	THD = 10%;	15	30		mW
Po	Transient Output Power	THD = 10% RL = 16Ω		50		mW
G∨	Close Loop Gain	P _o = 5mW	28	31	34	dB
THD	Total Harmonic Distortion	$P_o = 5mW$		0.2	1	%
Ct	Cross Talk	Rg = $10K\Omega$; P _o = $5mW$	40	50		dB
SVR	Ripple Rejection	V_r = 100mVrms, f = 100Hz Vol. control = 1/3V _{ref} C_{SVR} = 100 μ F; R_g =600 Ω		47		dB
	Volume Control Range		66	75		dB

Figure 1: Application Circuit

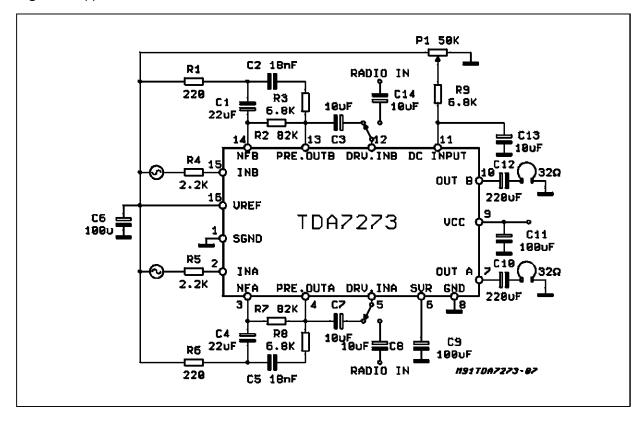


Figure 2: P.C. Board and Component Layout of the Circuit of Figure 1 (1:1 scale)

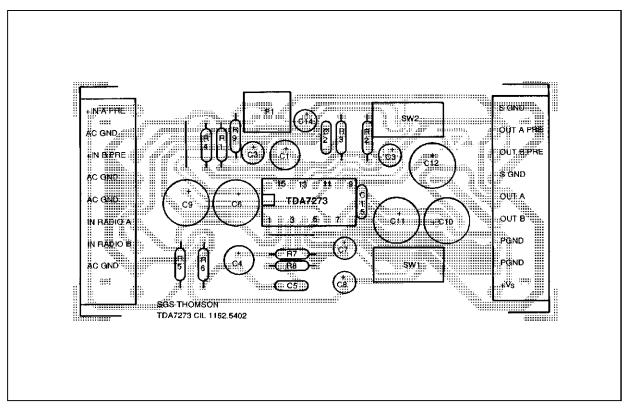


Figure 3: Supply Current vs. Supply Voltage (Preamplifier + Driver)

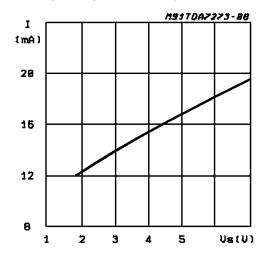


Figure 5: Closed Loop Gain vs. Frequency $(V_S = 3V)$ (PREAMPLIFIER)

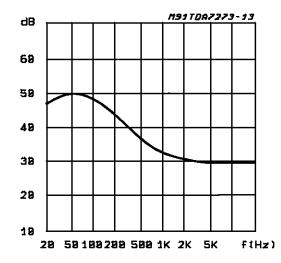


Figure 7: SVR vs. Frequency (PREAMPLIFIER)

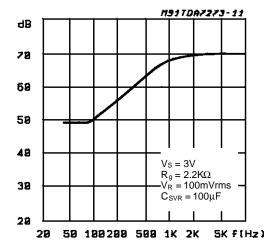


Figure 4: V_{ref}, vs. Supply Voltage (pin 16)

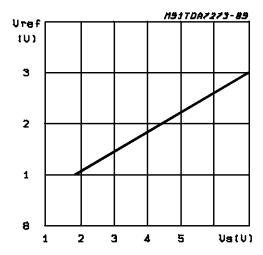


Figure 6: THD vs. Frequency ($V_S = 3V$, $V_o = 330 \text{mVrms}$, $R_L = 10 \text{K}\Omega$) (PREAMPLIFIER)

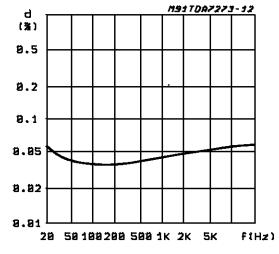


Figure 8: Quiescent Output Voltage vs. Supply Voltage (DRIVER)

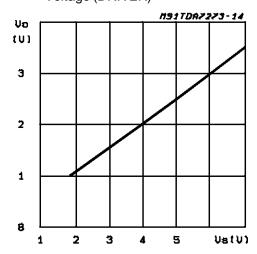


Figure 9: Closed Loop Gain vs Frequency $(V_S = 3V, R_L = 32\Omega)$ (DRIVER)

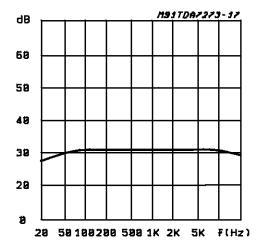


Figure 11: THD vs. Output Power ($V_0 = 2/3V_{ref}$, $V_S = 3V$, $R_L = 32\Omega$, f = 1KHz) (DRIVER)

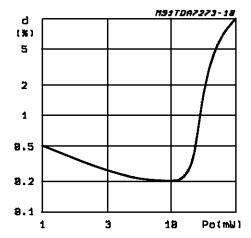


Figure 13: SVR vs. Frequency $V_S = 3V$ (R_L = 32Ω , $V_r = 100V$ rms $R_g = 600\Omega$, $C_{SVR} = 100$ mV) (DRIVER)

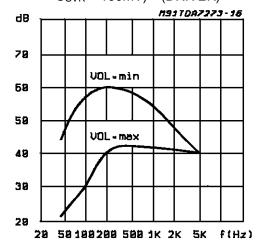


Figure 10: Output Power vs. Supply Voltage (Vol = $2/3V_{ref}$, R_L = 32Ω , THD = 10%, f = 1KHz) (DRIVER)

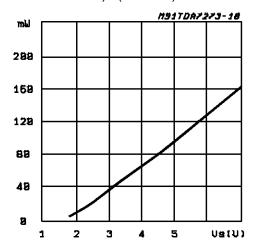


Figure 12: THD vs. Frequency ($P_0 = 5$ mW, $V_S = 3V R_L = 32\Omega$) (DRIVER)

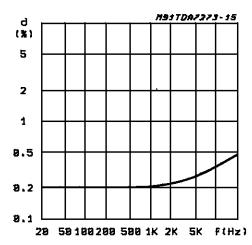
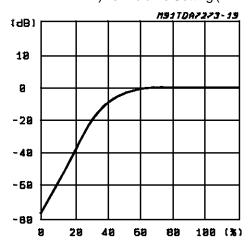
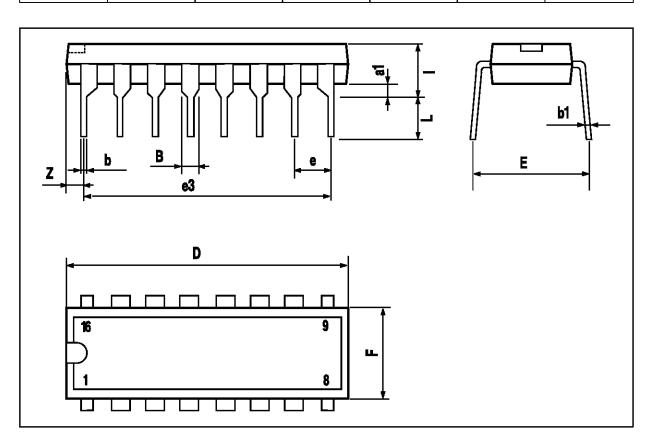


Figure 14: Volume Control (0dB = 10mW, $V_S = 3V R_{Vol} = 50K\Omega$, $R_L = 32\Omega$, f = 1KHz) vs. Volume Setting (DRIVER)



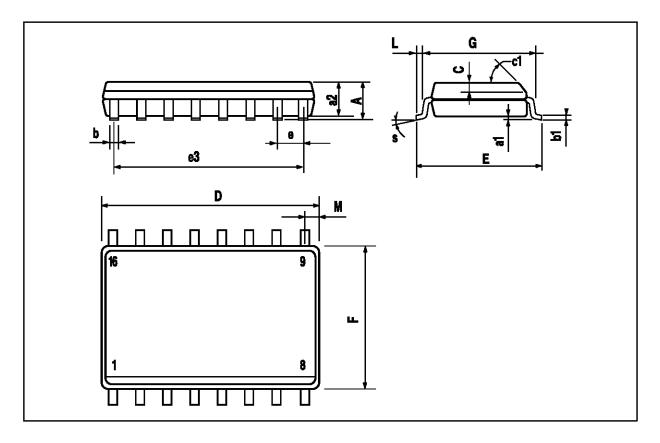
DIP16 PACKAGE MECHANICAL DATA

DIM.		mm				
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
ı			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



SO16 PACKAGE MECHANICAL DATA

DIM.		mm			inch	
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			2.65			0.104
a1	0.1		0.2	0.004		0.012
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.013
С		0.5			0.020	
c1			45°	(typ.)		
D	10.1		10.5	0.398		0.413
E	10.0		10.65	0.394		0.419
е		1.27			0.050	
e3		8.89			0.350	
F	7.4		7.6	0.291		0.299
L	0.5		1.27	0.020		0.050
М			0.75			0.030
S			8° (r	nax.)		



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thaliand - United Kingdom - U.S.A.

